Diode Semiconductor Device - Page 1 of 1



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Inclosure Materia	ıl:
Metal	
Overall Length:	
0.700 inches	
Overall Diameter	
Between 1.090 inc	shes and 1.150 inches
Mounting Facility	v Quantity:
1	
Mounting Method	1:
Threaded stud	
Features Provide	d:
Hermetically seale	ed case
Thread Size:	
0.312 inches	
Semiconductor N	laterial:
Silicon	
Voltage Rating In	Volts Per Characteristic:
450.0 reverse vol	tage, dc
Current Rating Po	er Characteristic:
900.00 amperes f	orward current, peak total value
Power Rating Per	r Characteristic:
200.0 watts total p	power dissipation
Maximum Operat	ing Tempurature Per Measurement Point:
150.0 degrees cel	sius ambient air
Test Data Docum	ent:
82577-925414 dra	wing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.
excludes any spec	ification, standard or other document that may be referenced in a basic governing drawing)
Thread Series De	signator:
Unc	
Terminal Type Ar	nd Quantity:
1 threaded stud ar	nd 1 tab, solder lug
Shelf Life:	
N/a	
Unit Of Measure:	
Demilitarization:	
No	
Fiig:	
A110a0	